

ABSTRACT

Embodiments of the present application provide a circuit for receiving data, a system for receiving data, and a memory device. The circuit for receiving data includes: a first amplification module, including: an amplification unit, provided with a first node, a second node, a third node, and a fourth node; a first N-channel metal oxide semiconductor (NMOS) transistor and a second NMOS transistor, the first NMOS transistor being provided with one terminal connected to the first node and another terminal connected to one terminal of the second NMOS transistor, another terminal of the second NMOS transistor being connected to the second node, a gate of one of the first NMOS transistor and the second NMOS transistor being configured to receive a first complementary feedback signal, and a gate of the other one of the first NMOS transistor and the second NMOS transistor being configured to receive an enable signal; and a third NMOS transistor and a fourth NMOS transistor, the third NMOS transistor being provided with one terminal connected to the third node and another terminal connected to one terminal of the fourth NMOS transistor, another terminal of the fourth NMOS transistor being connected to the fourth node, a gate of one of the third NMOS transistor and the fourth NMOS transistor being configured to receive a second complementary feedback signal, and a gate of the other one of the third NMOS transistor and the fourth NMOS transistor being configured to receive the enable signal; and a second amplification module. The embodiments of the present application at least facilitate accelerating the processing speed of the circuit for receiving data to the data signal while improving the receiving performance of the circuit for receiving data.